



Product Description

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Pin Description

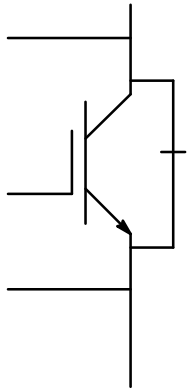


Figure 1. Pin Description

VE-Trac™ Direct Module NVH640S75L4SPC

MODULE CHARACTERISTICS (T_{vj} = 25°C, Unless Otherwise Specified)

Symbol	Parameter	Rating	Unit
T _{vj}	Operating Junction Temperature	-40 to 175	°C
T _{STG}	Storage Temperature	-40 to 125	°C
V _{ISO}	Isolation Voltage (DC, 0 Hz, 1 s)	4200	V
L _{sCE}	Stray Inductance	8	nH
RCC'+EE'	Module Lead Resistance, Terminals – Chip	0.8	mΩ
G	Module Weight	700	g
CTI	Comparative Tracking Index	>200	–
d _{creep}	Creepage: Terminal to Heatsink Terminal to Terminal	9.0 9.0	mm
d _{clear}	Clearance: Terminal to Heatsink Terminal to Terminal	4.5 4.5	mm

Symbol	Parameters	Conditions	Min	Typ	Max	Unit
Δp	Pressure Drop in Cooling Circuit					

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CHARACTERISTICS OF INVERSE DIODE ($T_{vj} = 25^{\circ}\text{C}$, Unless Otherwise Specified)

Symbol	Parameters	Conditions	Min	Typ	Max	Unit	
V_F	Diode Forward Voltage (Terminal)	$I_F = 450\text{ A}$	$T_{vj} = 25^{\circ}\text{C}$	–	1.70	2.02	V
	Diode Forward Voltage (Chip)	$I_F = 450\text{ A}$	$T_{vj} = 25^{\circ}\text{C}$	–	1.59	1.91	
			$T_{vj} = 150^{\circ}\text{C}$	–	1.54	–	
		$I_F = 640\text{ A}$	$T_{vj} = 175^{\circ}\text{C}$	–	1.51	–	
			$T_{vj} = 25^{\circ}\text{C}$	–	1.79	–	
			$T_{vj} = 150^{\circ}\text{C}$	–	1.80	–	
			$T_{vj} = 175^{\circ}\text{C}$	–	1.81	–	
E_{rr}	Reverse Recovery Energy	$I_F = 450\text{ A}$, $V_R = 400\text{ V}$, $V_{GE} = -8\text{ V}$, $R_{g,on} = 2.8\ \Omega$	$di/dt = 2.8\text{ A/ns}$, T_{vj}				

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TYPICAL CHARACTERISTICS

VE-Trac™ Direct Module NVH640S75L4SPC

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PACKAGE DIMENSIONS

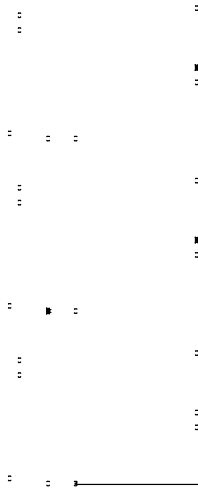
SSDC33, 154.50x92.0 (SPC)
CASE 183AC
ISSUE A

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VE-Trac™ Direct Module NVH640S75L4SPC

PACKAGE DIMENSIONS

SSDC33, 154.50x92.0 (SPC)
CASE 183AC
ISSUE A



VE-Trac™ Direct Module NVH640S75L4SPC